

Raman-based Quantitative Point Defect Density Comparison in Graphenic System

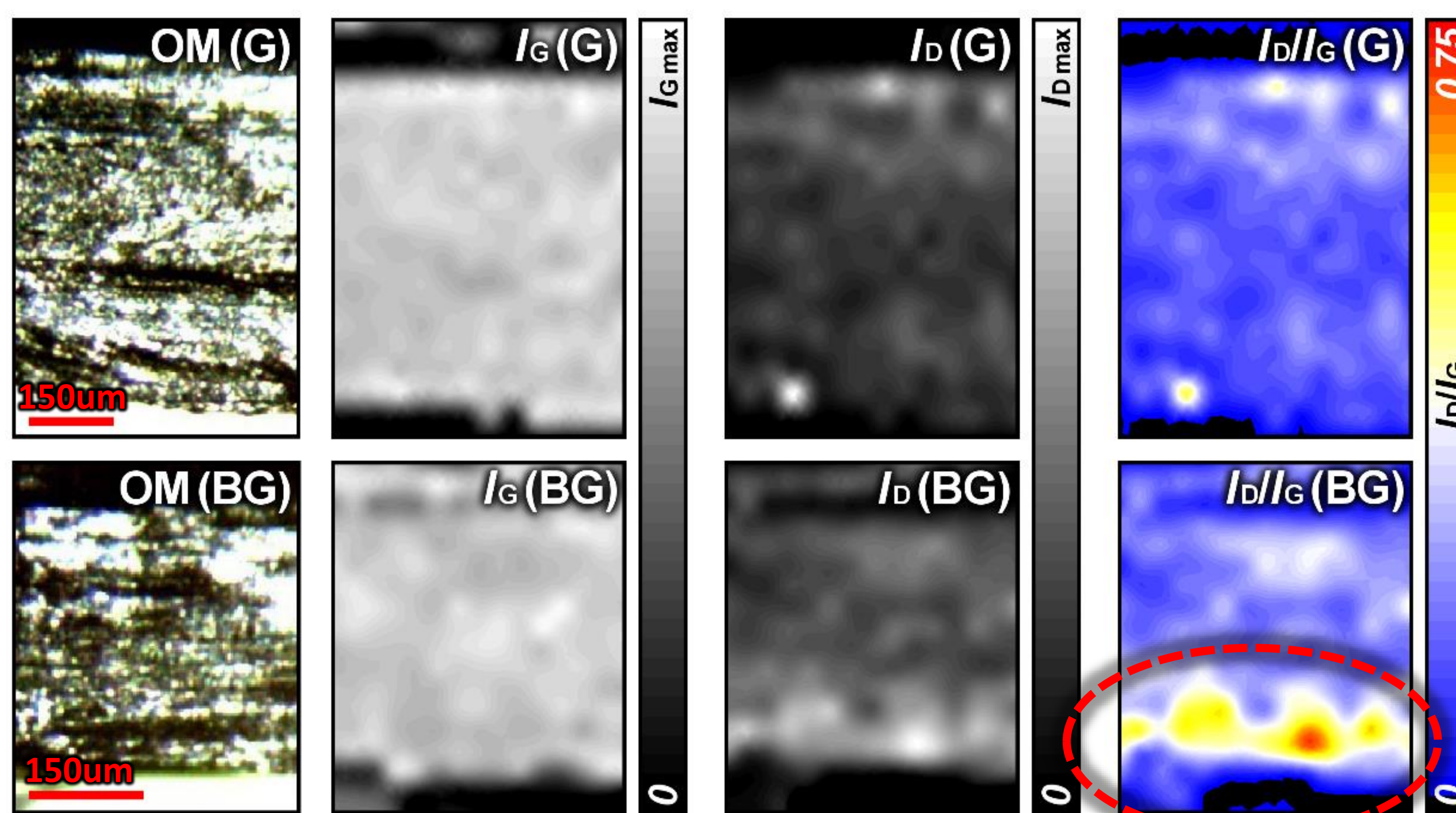
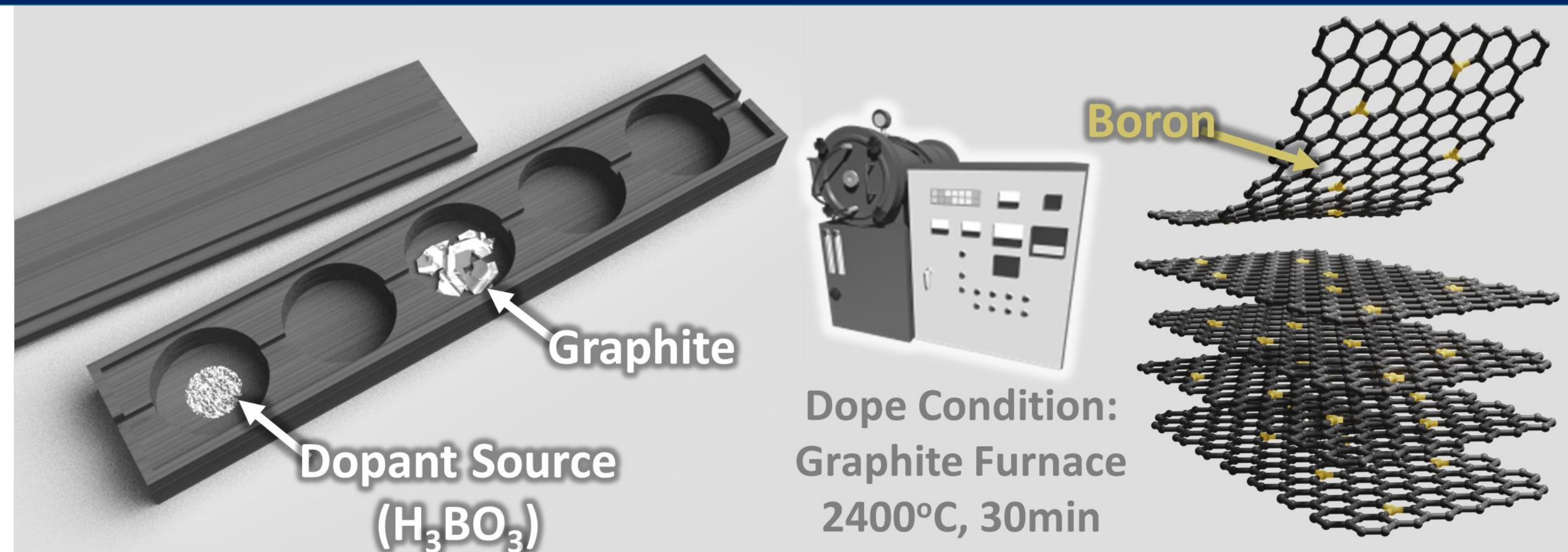
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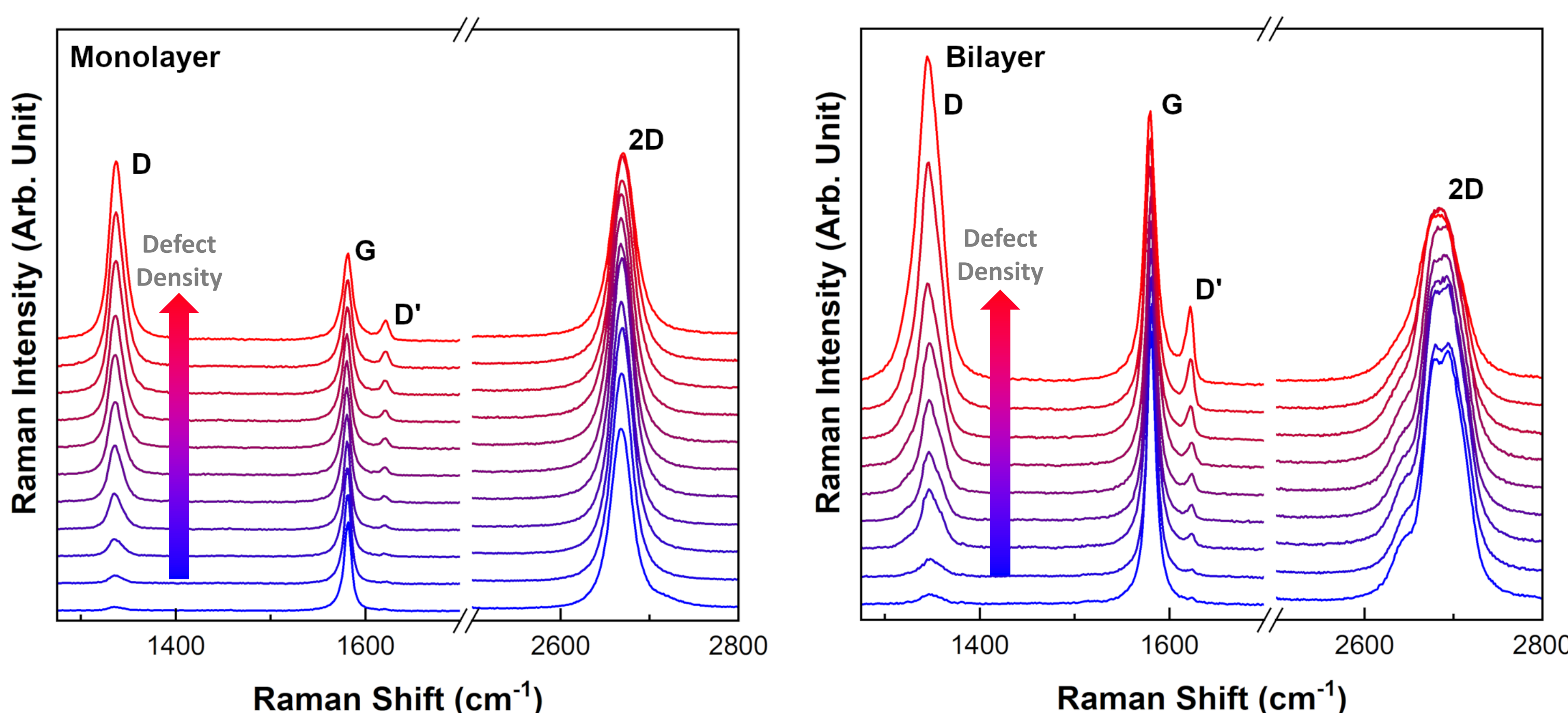


Although exhaustive efforts have been devoted to understanding the correlation between Raman feature and defect density and layer count [1], a unified solution for the defect density evaluation in graphenic materials has not yet been proposed. In this study, following the previous report [2], the substitutional boron atoms were introduced into bulk graphite flake using thermal diffusion of a boron atom. After doping process, mechanical exfoliation was performed to obtain mono-to-few-layered graphenic materials. Detailed Raman spectroscopic analysis and collected more than 10k spectra revealed that data collected from graphenic materials that possess the same defect density (n_D) form a line on the plane of $A_D/A_G - A_{2D}/A_G$. Finally, a generalized equation to calculate defect density (n_D) or average inter-defect distance (L_D) was proposed.

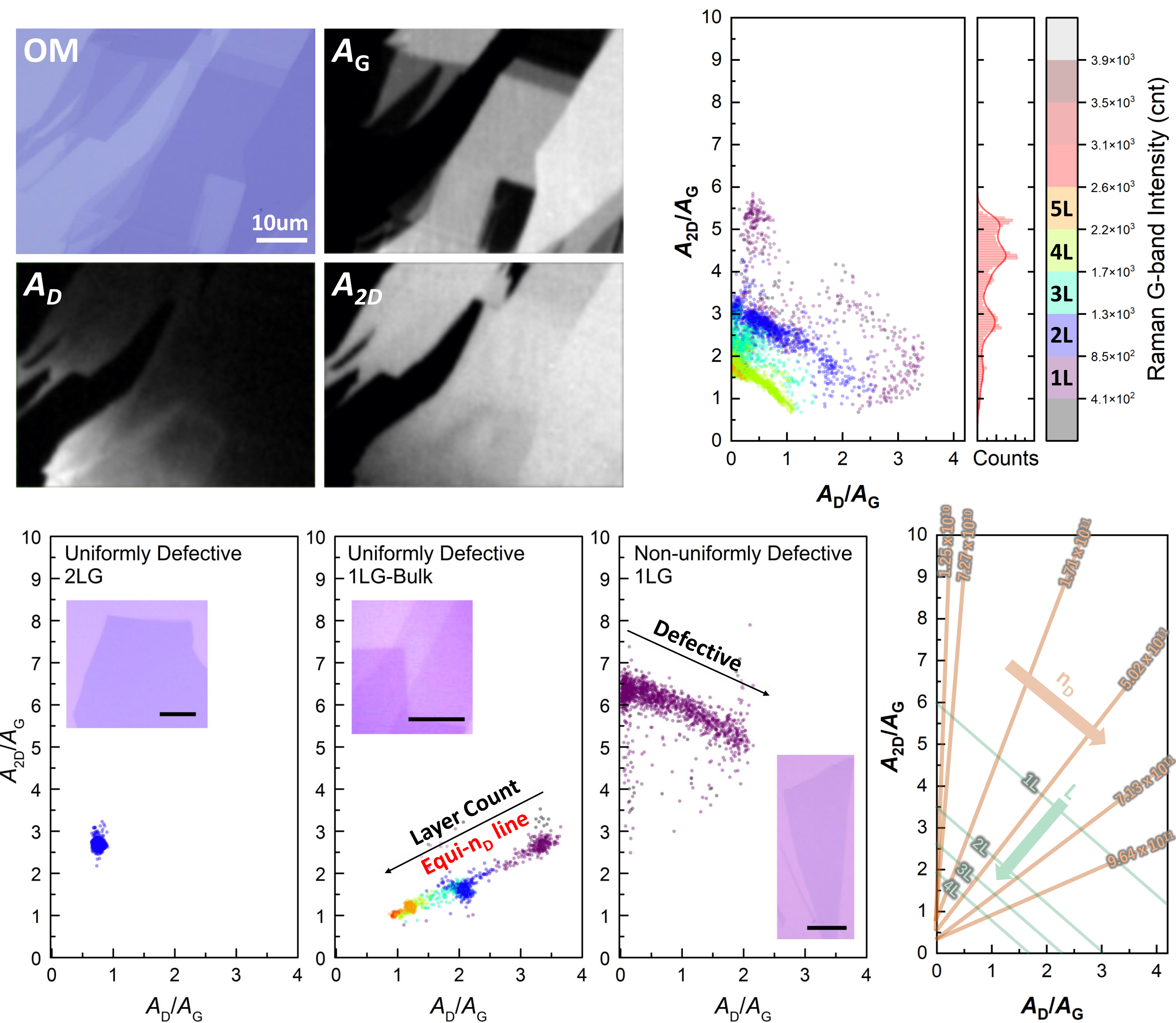
High Quality Doped-Graphite



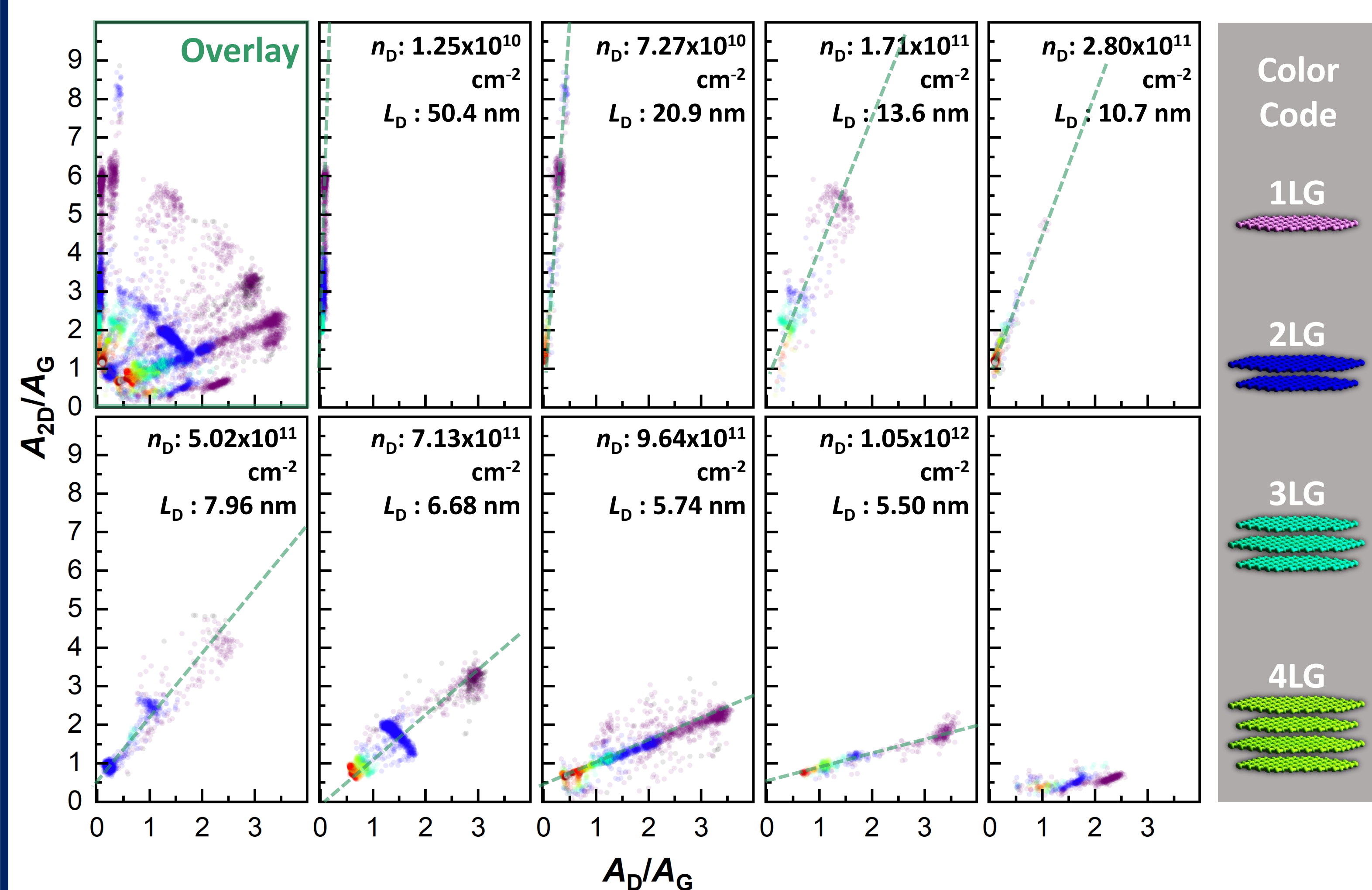
Exfoliated Doped-Graphene



Raman Data Pattern Analysis



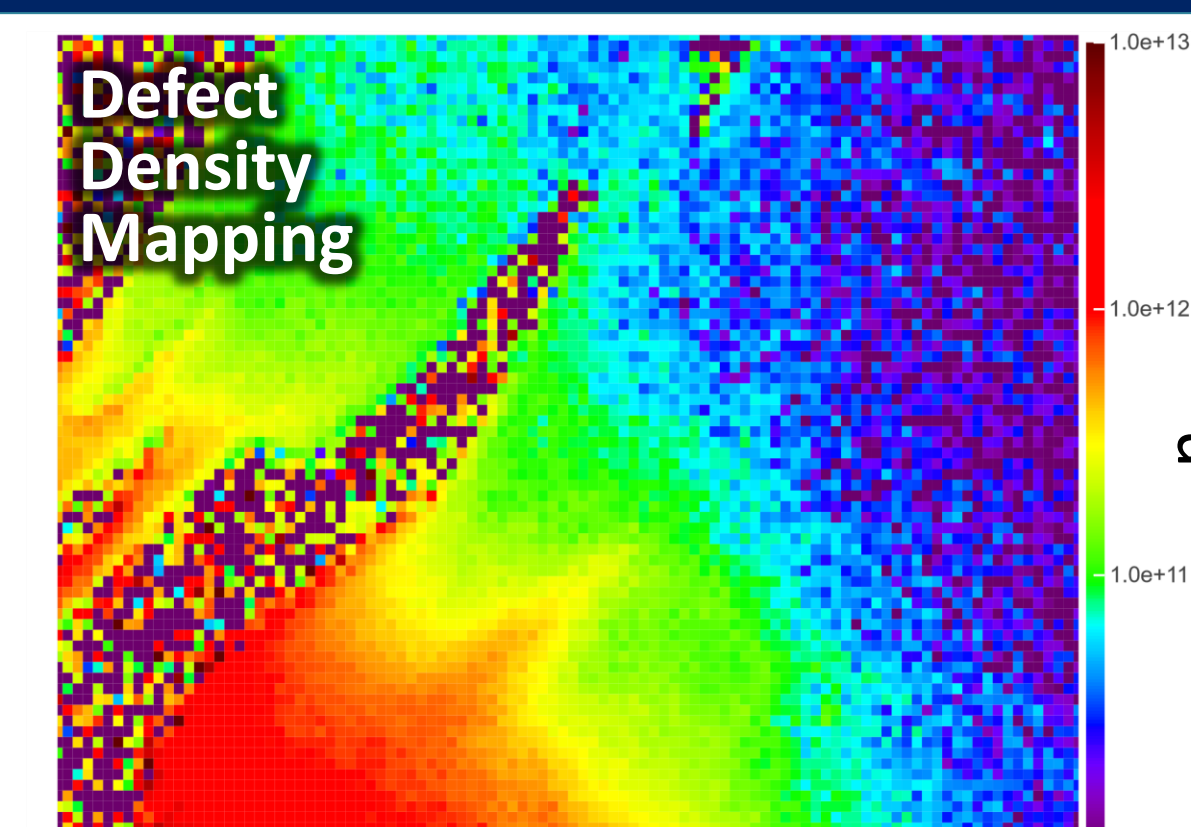
Experimental Calibration of Equi- n_D Line



Conclusion

$$\left(\frac{A_{2D}}{A_G}\right) = \frac{(L_D^2)^{1.13}}{92.1} \left(\frac{A_D}{A_G}\right) + 0.533, L_D \text{ (nm)}$$

$$\left(\frac{A_{2D}}{A_G}\right) = \frac{1}{92.1} \left(\frac{10^{14}}{\pi n_D}\right)^{1.13} \left(\frac{A_D}{A_G}\right) + 0.533, n_D \text{ (cm}^{-2}\text{)}$$



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REFERENCES

- [1]. Cançado, L. G. et al. Nano Lett. 11 (2011), 3190–3196.
- [2]. Kim, Y. A. et al. ACS Nano 6 (2012), 6293–6300.